

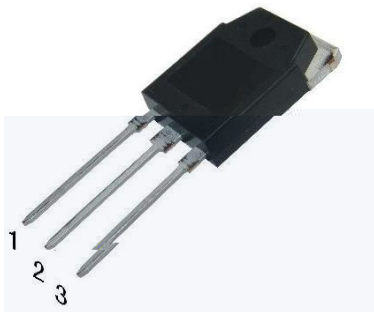
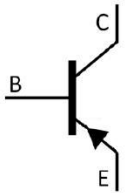
Rev.A Nov.-2018

TO-3P PNP Silicon PNP transistor in a TO-3P Plastic Package.

100W NJW0281GC

Recommend for 100W high fidelity audio frequency amplifier output stage, Complementary to NJW0281GC.

Power amplifier applications.



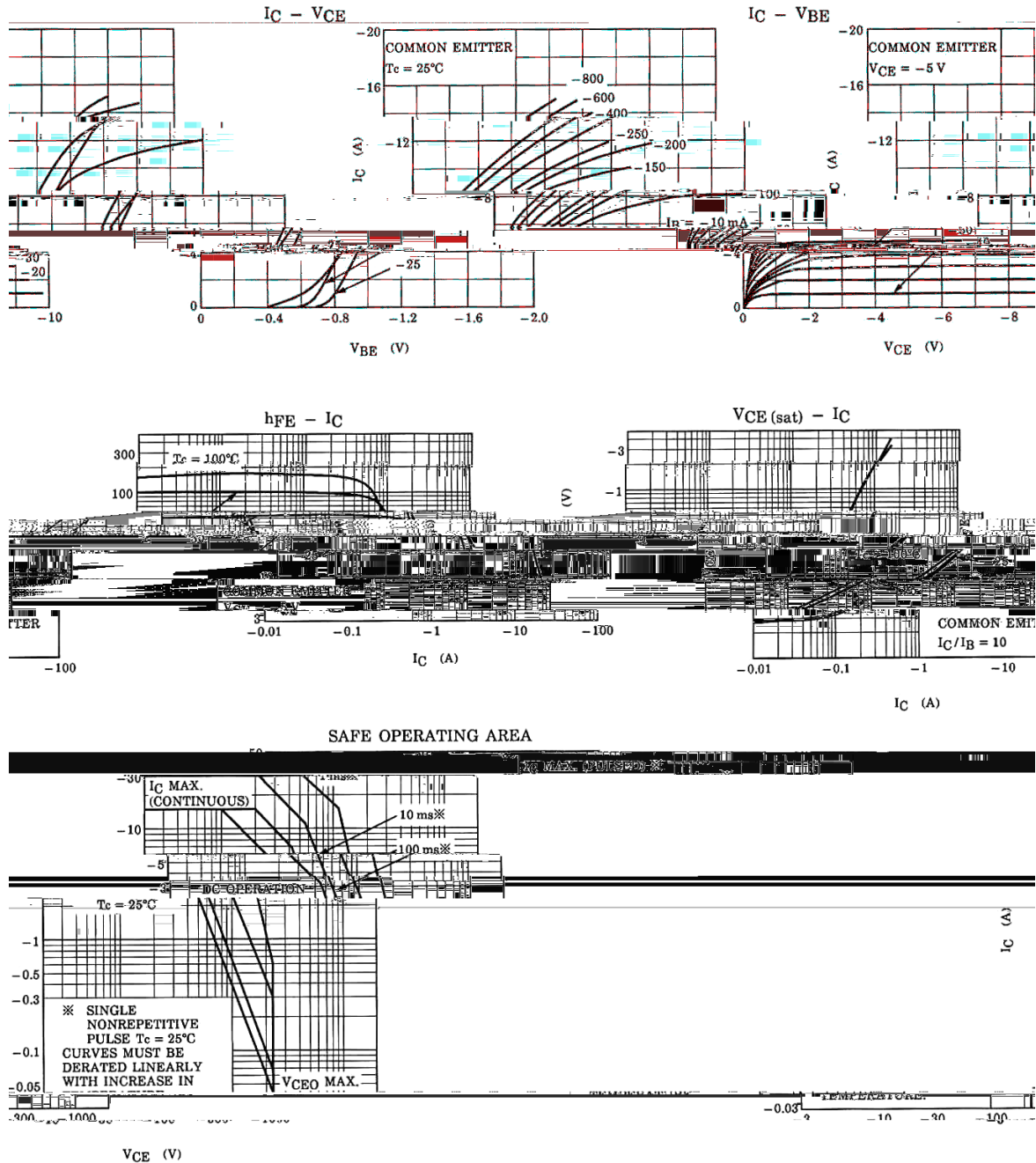
PIN1 Base PIN 2 Collector PIN 3 Emitter

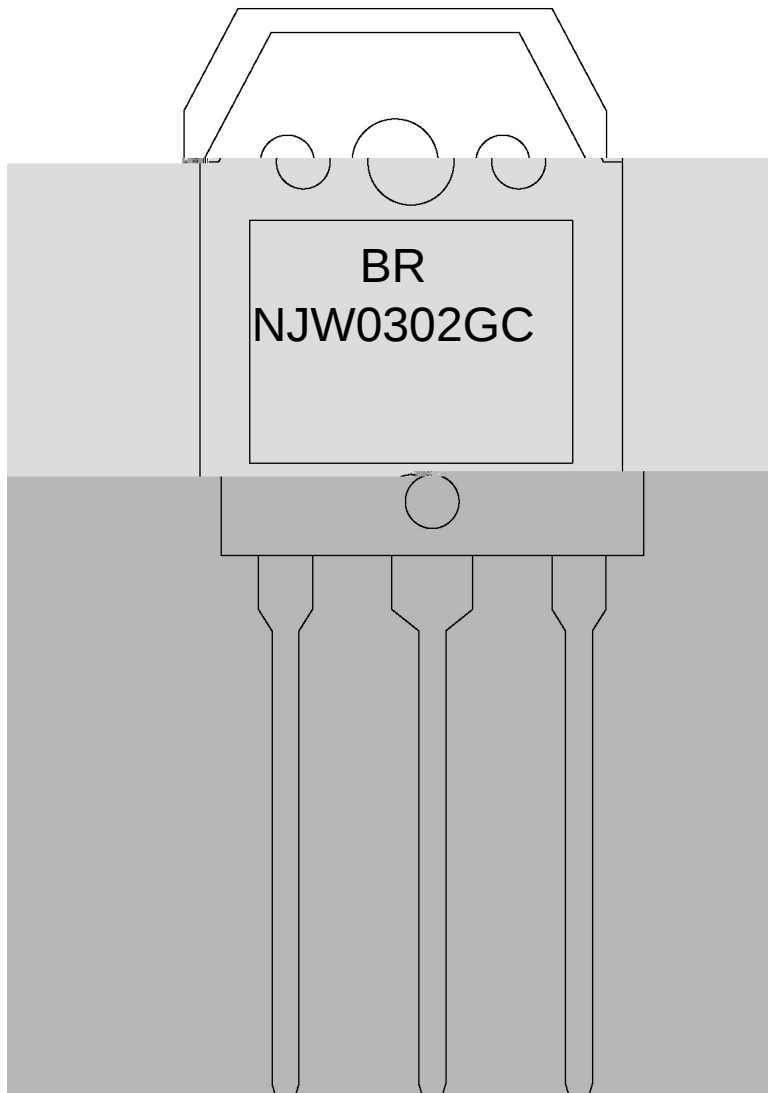
See Marking Instructions.

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-360	V
Collector to Emitter Voltage	V_{CEO}	-360	V
Emitter to Base Voltage	V_{EBO}	-5	V
Collector Current - Continuous	I_C	-15	A
Peak Collector Current	I_{CP}	-30	A
Base Current	I_B	-1.5	A
Collector Power Dissipation	$P_{C(TC=25)}$	150	W
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Emitter Breakdown Voltage	V_{CEO}	$I_C=-50mA$ $I_B=0$	-360			V
Collector Cut-Off Current	I_{CBO}	$V_{CB}=-230V$ $I_E=0$			-5.0	μA
Emitter Cut-Off Current	I_{EBO}	$V_{EB}=-5.0V$ $I_C=0$			-5.0	μA
DC Current Gain	$h_{FE(1)}$	$V_{CE}=-5.0V$ $I_C=-1.0A$	55		160	
	$h_{FE(2)}$	$V_{CE}=-5.0V$ $I_C=-7.0A$	35	80		
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=-8.0A$ $I_B=-0.8A$		-1.5	-3.0	V
Base to Emitter Voltage	V_{BE}	$V_{CE}=-5.0V$ $I_C=-7.0A$		-1.2	-1.5	V
Transition Frequency	f_T	$I_C=-1.0A$ $V_{CE}=-5.0V$		30		MHz
Collector output capacitance	C_{ob}	$V_{CB}=-10V$ $I_E=0$ $f=1.0MHz$		360		pF

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BR

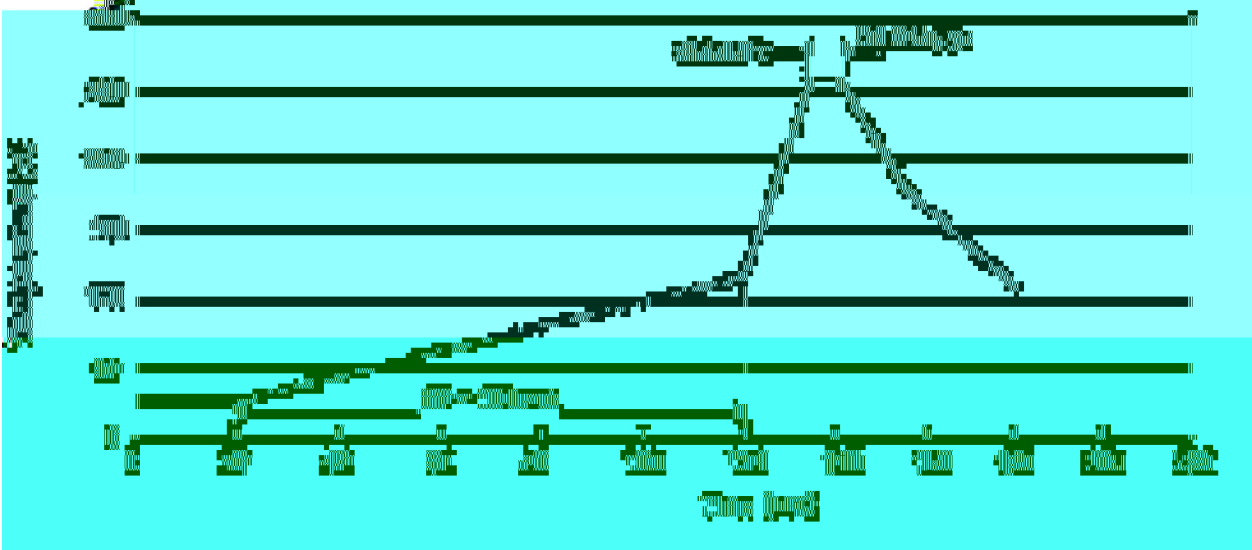
NJW0302GC

Note:

BR: Company Code.

NJW0302GC: Product Type.

****: Lot No. Code, code change with Lot No.



Note:			
1	25 150	60 90sec;	1.Preheating:25~150 , Time:60~90sec.
2	255±5	5±0.5sec;	2.Peak Temp.:255±5 , Duration:5±0.5sec.
3	2 10	/sec.	3. Cooling Speed: 2~10 /sec.

270±5	10±1 sec.	Temp.:270±5	Time:10±1 sec
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/ TUBE

Package Type 封装形式	Units 包装数量	Dimension 包装尺寸 (unit: mm ³)
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